30V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

NEW PRODUCT

Product Summary

$V_{(BR)DSS}$	$R_{DS(ON)}$ max	I_D max T_C = +25°C
30V	4mΩ@V_{GS} = 10V	75A
	7mΩ@V_{GS} = 4.5V	75A

Features

- Low On-Resistance
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

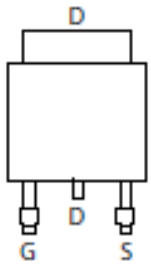
Mechanical Data

- Case:TO252
- Case Material: Molded Plastic, "Green" Molding Compound.
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Matte Tin Finish.
  Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.315 grams (Approximate)

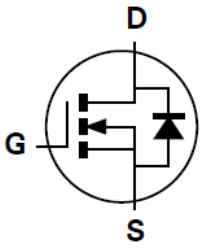
Applications

- Power Management Functions
- DC-DC Converters
- Backlighting

Top View



Pin Out Top View



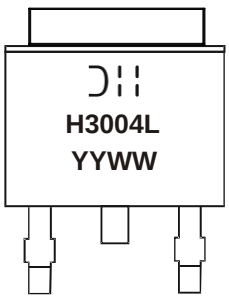
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH3004LK3-13	TO252	2500/Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



=Manufacturer's Marking
H3004L = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 15 = 2015)
WW = Week Code (01 to 53)

NEW PRODUCT

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	+20 -16	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_C = +25°C T_C = +70°C	I_D	75 75	A
	Steady State	T_A = +25°C T_A = +70°C	I_D	21 17	A
Pulsed Drain Current (380µs Pulse, Duty Cycle=1%)			I_{DM}	160	A
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	3	A
Avalanche Current (Note 7) L=5mH			I_{AS}	10.7	A
Avalanche Energy (Note 7) L=5mH			E_{AS}	287	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		P_D	1.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady state	$R_{\theta JA}$	80	°C/W
Total Power Dissipation (Note 6)		P_D	3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	$R_{\theta JA}$	50	°C/W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	1.4	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	-	-	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	-	-	10	µA	V_{DS} = 24V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	100 -100	nA	V_{GS} = +20V, V_{DS} = 0V V_{GS} = -16V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	-	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	3.3	4	mΩ	V_{GS} = 10V, I_D = 20A
		-	5.5	7		V_{GS} = 4.5V, I_D = 7A
Diode Forward Voltage	V_{SD}	-	0.75	1	V	V_{GS} = 0V, I_S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	-	2370	-	pF	V_{DS} =15V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	-	1360	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	240	-	pF	
Gate Resistance	R_g	-	0.6	-	Ω	V_{DS} =0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	-	20	-	nC	V_{DS} = 15V, I_D =20A
Total Gate Charge (V_{GS} = 10V)	Q_g	-	44	-	nC	
Gate-Source Charge	Q_{gs}	-	7	-	nC	
Gate-Drain Charge	Q_{gd}	-	8	-	nC	
Turn-On Delay Time	$t_{D(ON)}$	-	6.2	-	ns	V_{DD} = 15V, V_{GS} = 10V, R_L = 0.75Ω, R_G = 3Ω, I_D =20A
Turn-On Rise Time	t_R	-	4.3	-	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	-	21	-	ns	
Turn-Off Fall Time	t_F	-	8	-	ns	
Reverse Recovery Time	t_{RR}	-	25	-	ns	I_F =15A, di/dt=500A/µs
Reverse Recovery Charge	Q_{RR}	-	37	-	nC	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

NEW PRODUCT

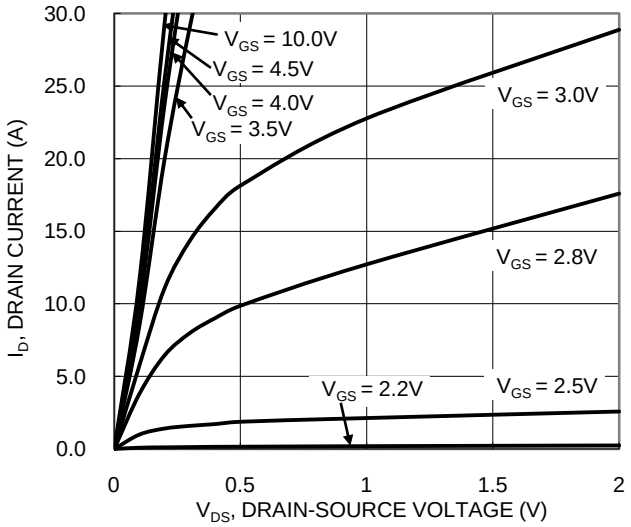


Figure 1. Typical Output Characteristic

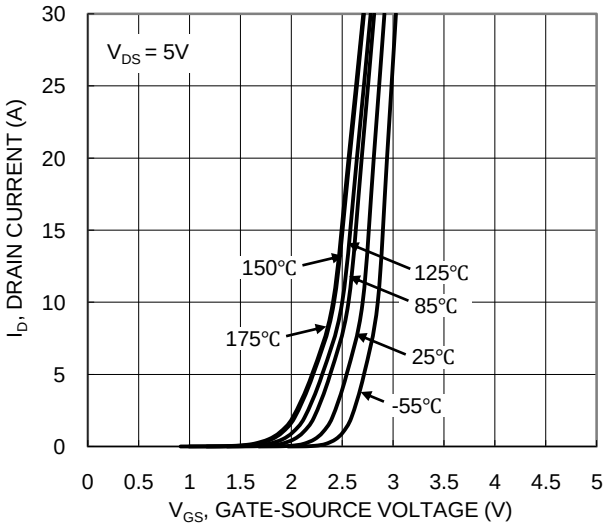


Figure 2. Typical Transfer Characteristic

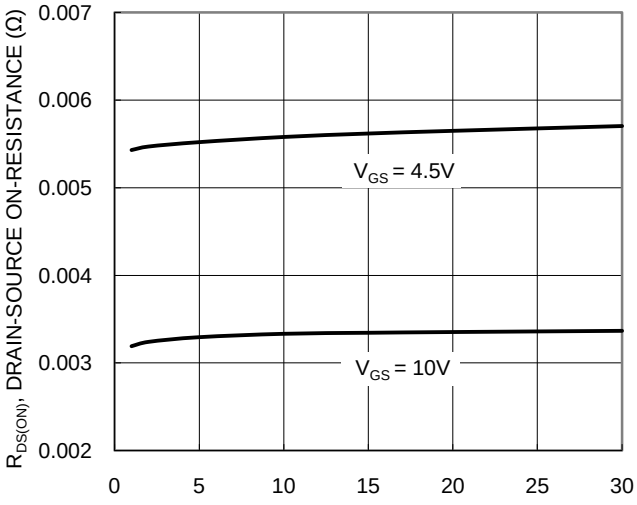


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

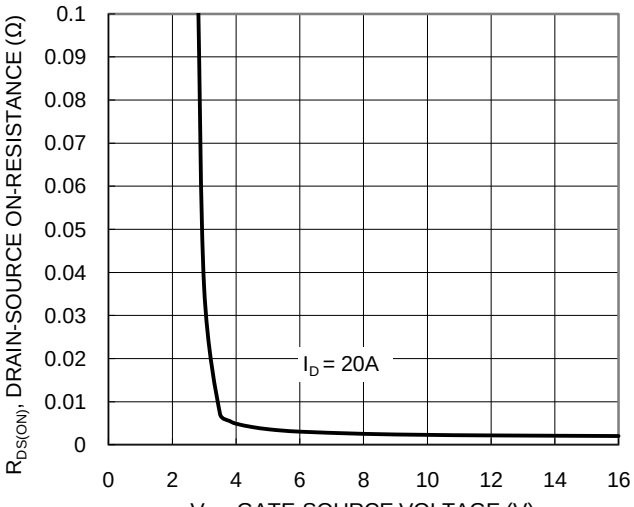


Figure 4. Typical Transfer Characteristic

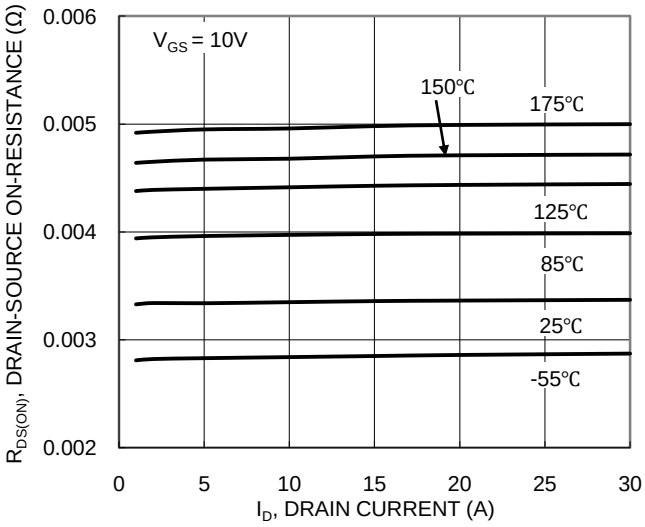


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

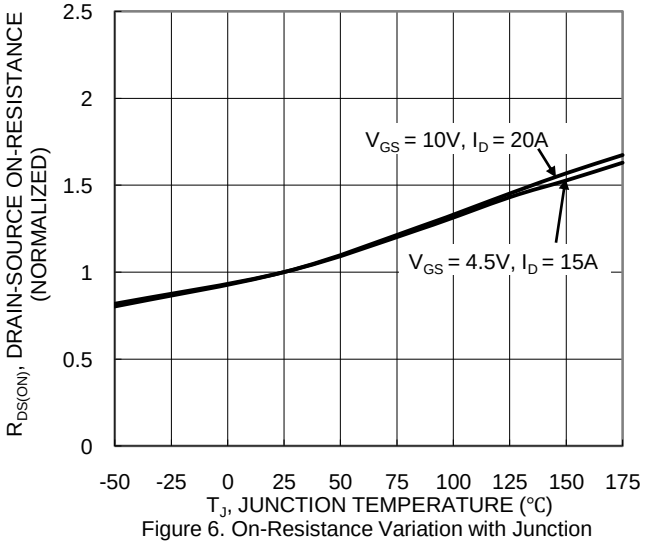


Figure 6. On-Resistance Variation with Junction Temperature

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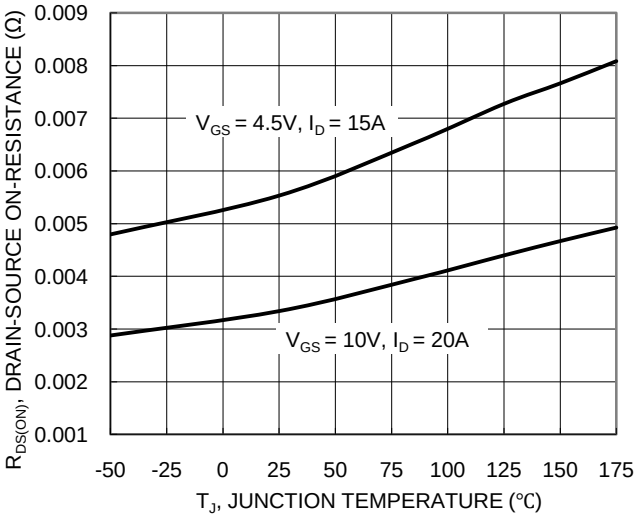

Figure 7. On-Resistance Variation with Junction Temperature

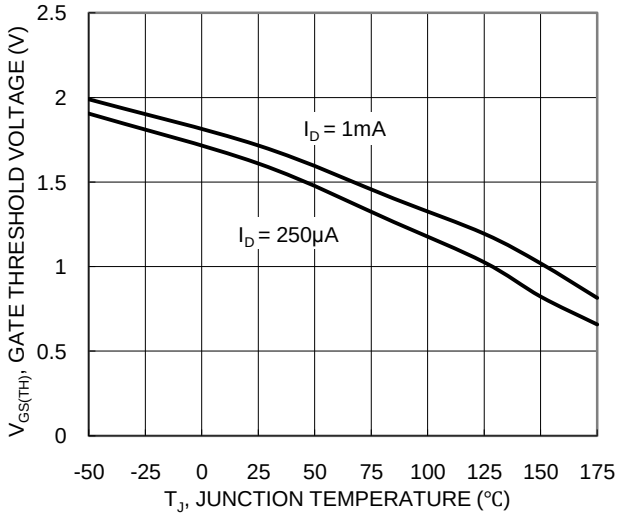

Figure 8. Gate Threshold Variation vs. Junction Temperature

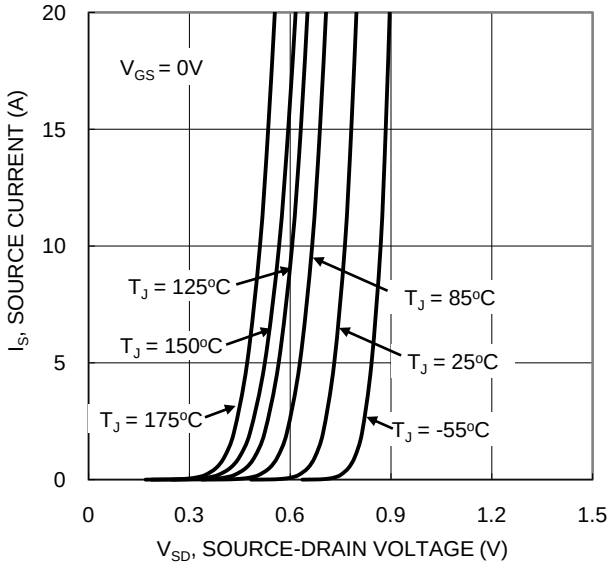

Figure 9. Diode Forward Voltage vs. Current

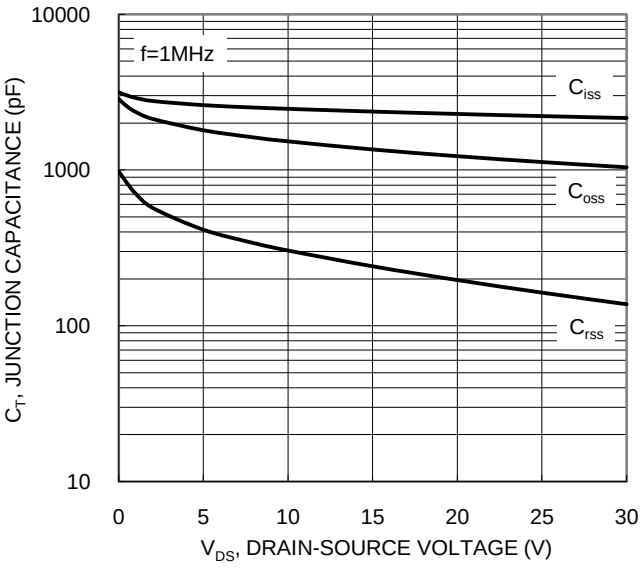

Figure 10. Typical Junction Capacitance

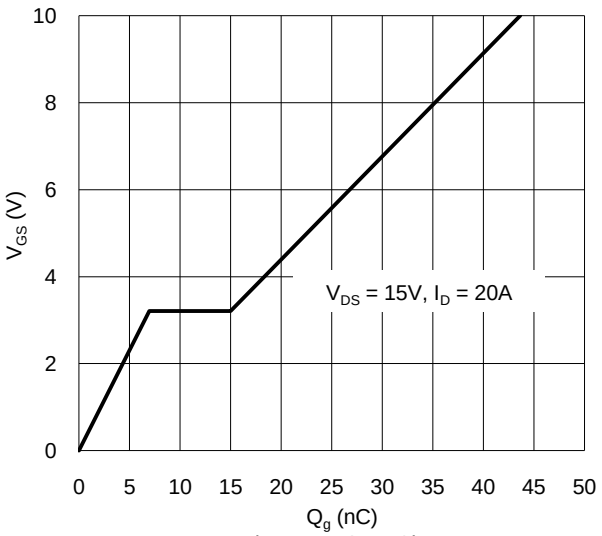

Figure 11. Gate Charge

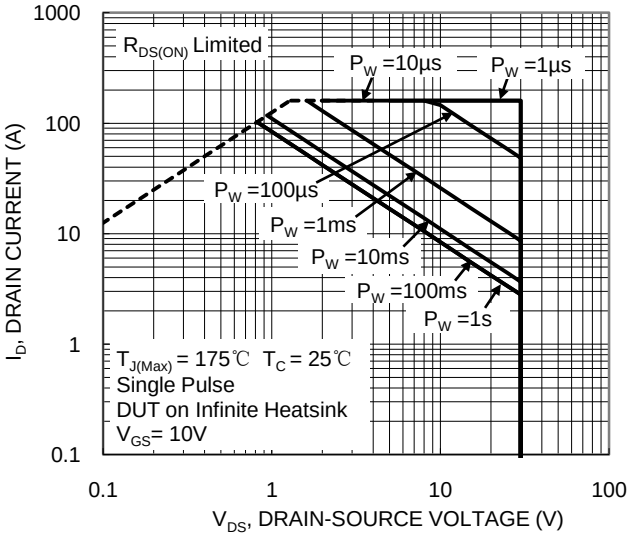

Figure 12. SOA, Safe Operation Area

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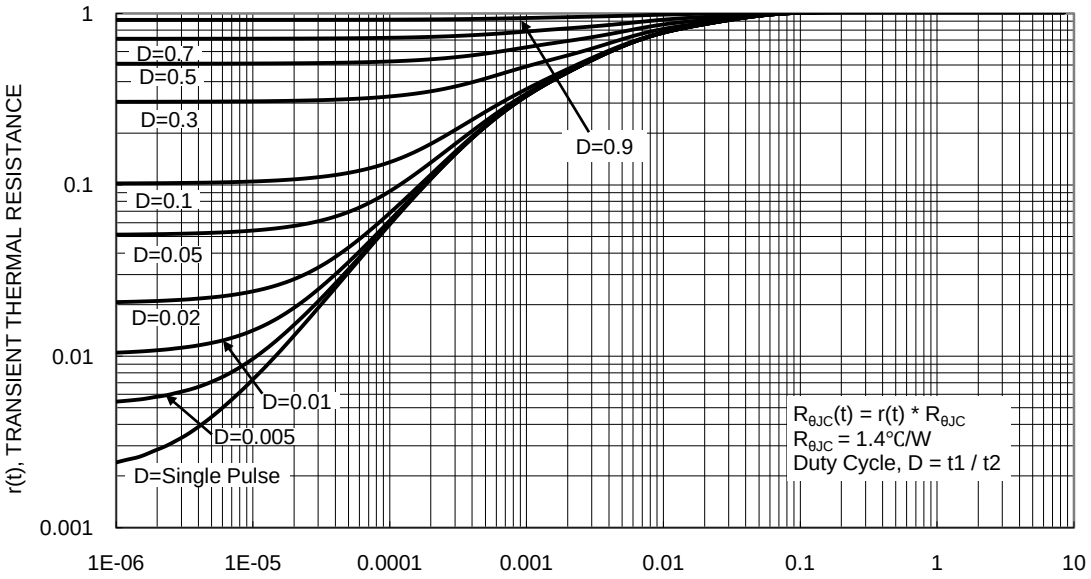
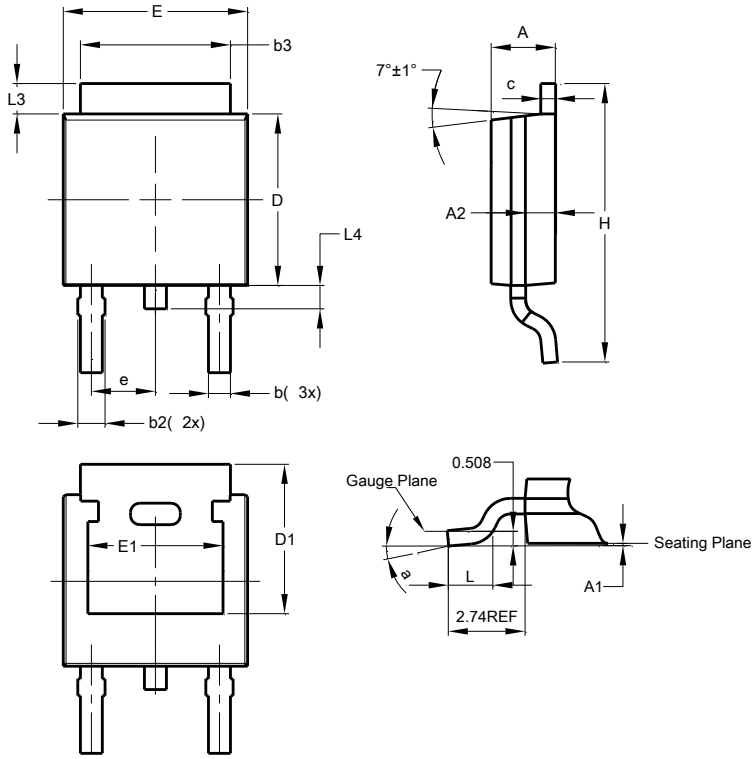


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

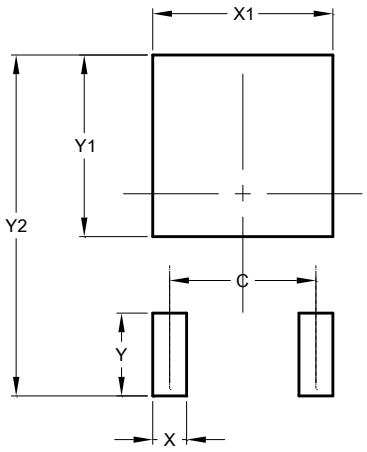


TO252 (DPAK)			
Dim	**Min**	**Max**	**Typ**
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.46	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	-	-
e	-	-	2.286
E	6.45	6.70	6.58
E1	4.32	-	-
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	-
All Dimensions in mm			

NEW PRODUCT

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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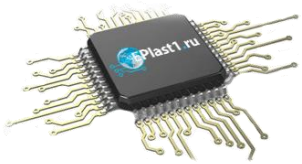
Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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